

**Features**

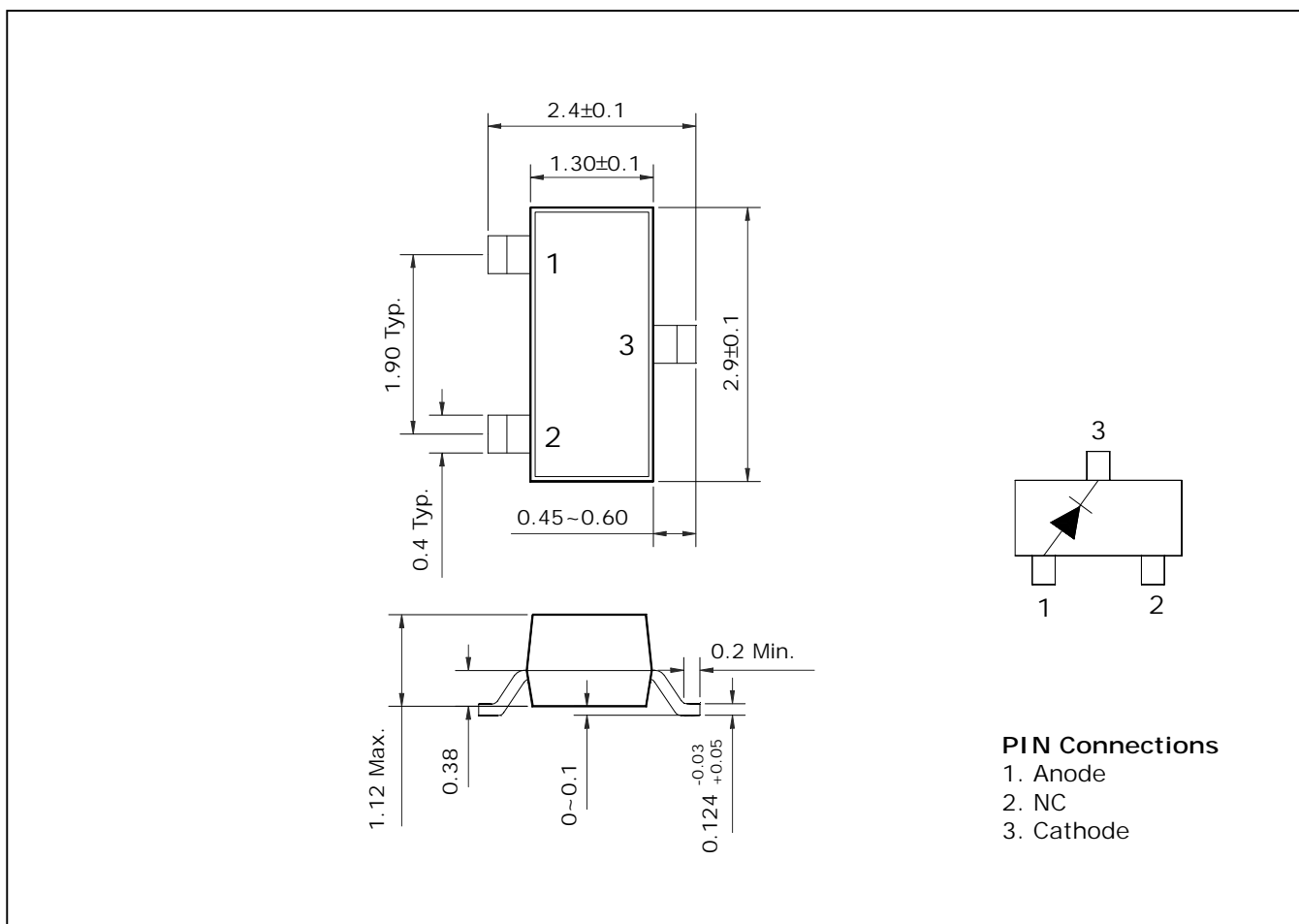
- Low power rectified
- Silicon epitaxial type
- High reliability

**Ordering Information**

Type No.	Marking	Package Code
SDB3101	DB1	SOT-23

**Outline Dimensions**

unit : mm



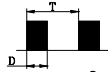
## Absolute maximum ratings

Ta=25°C

Characteristic	Symbol	Ratings	Unit
Reverse voltage	$V_R$	30	V
Repetitive peak forward current	$I_{FRM}^*$	0.5	A
Forward current	$I_F$	0.2	A
Non-repetitive peak forward current(10ms)	$I_{FSM}$	2	A
Power dissipation	$P_D$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ 150	°C

\* :  $\delta = D/T = 0.33$

(T<1S)



## Electrical Characteristics

Ta=25°C

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward voltage 1	$V_{F(1)}$	$I_F=10mA$	-	-	0.4	V
Forward voltage 2	$V_{F(2)}$	$I_F=30mA$	-	-	0.5	V
Reverse current	$I_R$	$V_R=30V$	-	-	1	μA
Total capacitance	$C_T$	$V_R=1V, f=1MHz$	-	-	10	pF
Reverse recovery time	$t_{rr}$	$I_F = I_R=10mA, I_{RR}= 1mA, R_L=100\Omega$	-	-	5	ns

Electrical Characteristic Curves

Fig. 1  $I_F$ - $V_F$

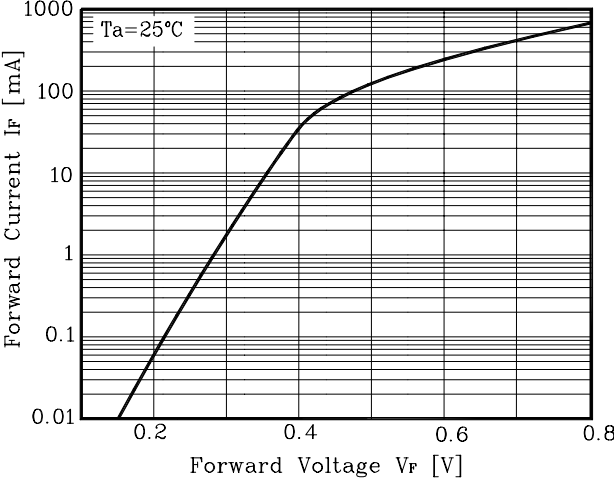


Fig. 2  $I_R$  - $V_R$

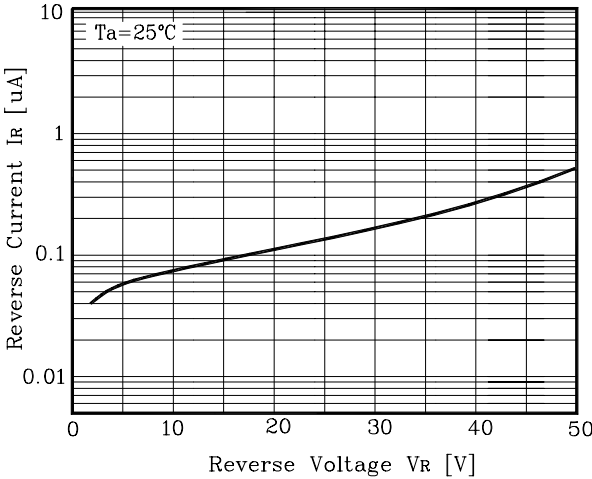


Fig. 3  $C_T$ - $V_R$

